

## P-Channel MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
- 15	0.021 at V <sub>GS</sub> = - 4.5 V	- 12.5	30 nC
	0.026 at V <sub>GS</sub> = - 2.5 V	- 11.0	
	0.033 at V <sub>GS</sub> = - 1.8 V	- 9.5	

### FEATURES

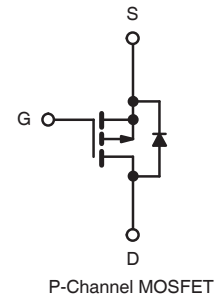
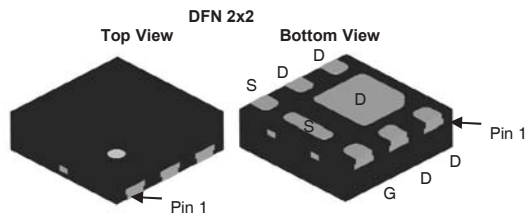
- Halogen-free according to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Ultra Small DFN2x2 Chipscale Packaging Reduces Footprint Area, Profile (0.62 mm) and On-Resistance Per Footprint Area
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- PA Switch
- Battery Switch
- Load Switch



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	- 15	V
Gate-Source Voltage	V <sub>GS</sub>	± 8	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	- 12.5
		T <sub>C</sub> = 70 °C	- 9.7
		T <sub>A</sub> = 25 °C	- 7.7 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	- 5.7 <sup>b, c</sup>
Pulsed Drain Current	I <sub>DM</sub>	- 36	A
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	
		T <sub>A</sub> = 25 °C	- 4.5 <sup>b, c</sup>
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	6.57
		T <sub>C</sub> = 70 °C	4.2
		T <sub>A</sub> = 25 °C	2.9 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	1.86 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C
Package Reflow Conditions <sup>d</sup>	IR/Convection	260	

Notes:

a. Based on T<sub>C</sub> = 25 °C.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. Refer to IPC/JEDEC (J-STD-020), no manual or hand soldering.

e. In this document, any reference to the Case represents the body of the DFN2X2 device and Foot is the bump.

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a, b</sup>	$R_{thJA}$	35	48	°C/W
Maximum Junction-to-Foot (Drain)	Steady State $R_{thJF}$	16	26	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. Maximum under steady state conditions is 72 °C/W.

SPECIFICATIONS ( $T_J = 25\text{ °C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 15			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		- 13.3		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		2.4			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 0.35		- 0.9	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 6\text{ V}$			- 100	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -12\text{ V}, V_{GS} = 0\text{ V}$			- 1	$\mu\text{A}$
		$V_{DS} = -12\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ °C}$			- 10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq 5\text{ V}, V_{GS} = -4.5\text{ V}$	- 20			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -1\text{ A}$		0.021	0.025	$\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -1\text{ A}$		0.026	0.029	
		$V_{GS} = -1.8\text{ V}, I_D = -1\text{ A}$		0.033	0.037	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -4\text{ V}, I_D = -1\text{ A}$		5.1		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -6\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		2000		pF
Output Capacitance	$C_{oss}$			737		
Reverse Transfer Capacitance	$C_{rss}$			521		
Total Gate Charge	$Q_g$	$V_{DS} = -6\text{ V}, V_{GS} = -5\text{ V}, I_D = -1\text{ A}$		38	57	nC
				35	53	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -6\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -1\text{ A}$		7.3		
Gate-Drain Charge	$Q_{gd}$			5.9		
Gate Resistance	$R_g$	$V_{GS} = -0.1\text{ V}, f = 1\text{ MHz}$		28		$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6\text{ V}, R_L = 4\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 6\text{ }\Omega$		14	21	ns
Rise Time	$t_r$			25	40	
Turn-Off Delay Time	$t_{d(off)}$			380	570	
Fall Time	$t_f$			240	360	

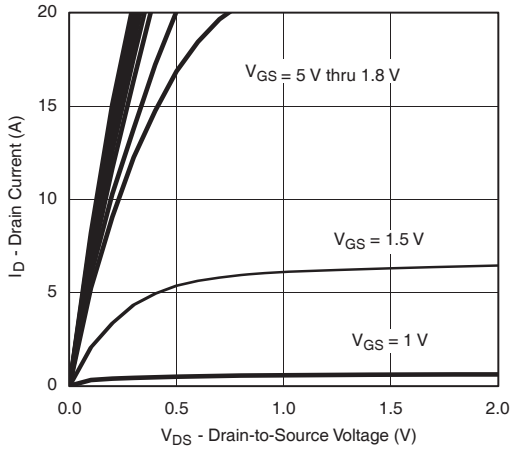
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			- 12.5	A
Pulse Diode Forward Current	$I_{SM}$				- 36	
Body Diode Voltage	$V_{SD}$	$I_S = -1\text{ A}, V_{GS} = 0\text{ V}$		- 0.65	- 1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = -1\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		311	467	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			1.136	1.705	$\mu\text{C}$
Reverse Recovery Fall Time	$t_a$			116		ns
Reverse Recovery Rise Time	$t_b$			195		

Notes:

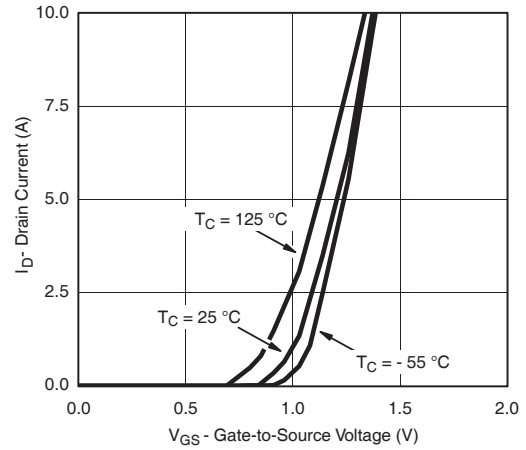
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

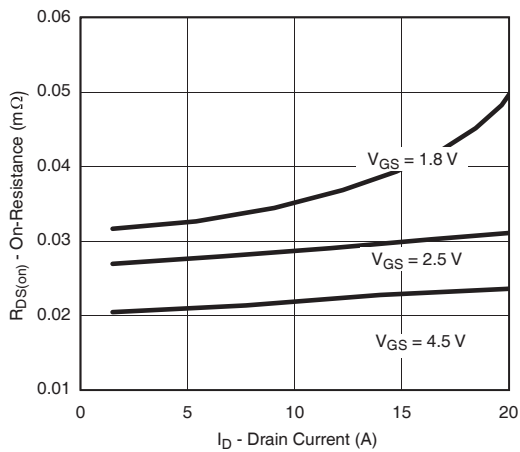
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



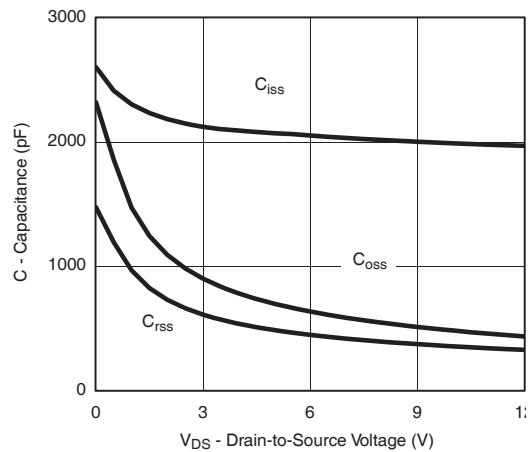
**Output Characteristics**



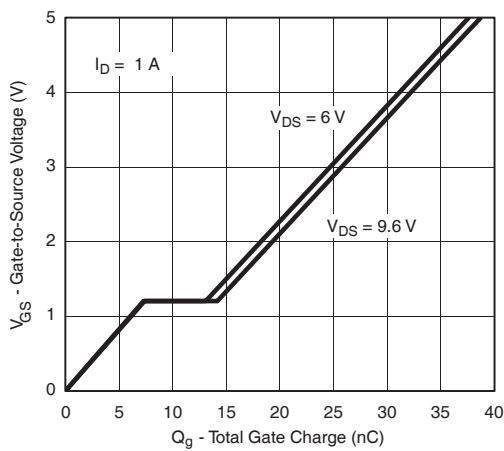
**Transfer Characteristics**



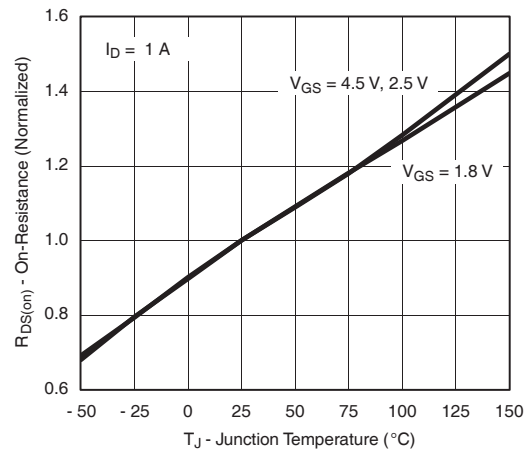
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**

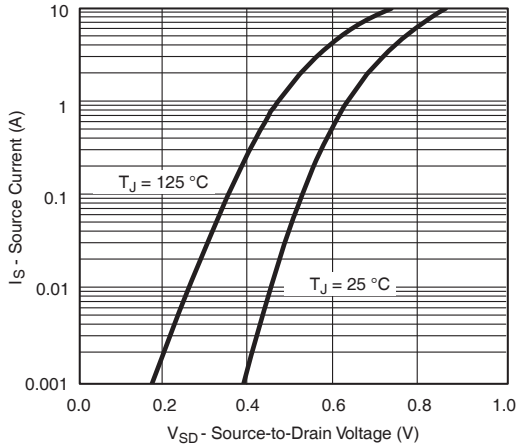


**Gate Charge**

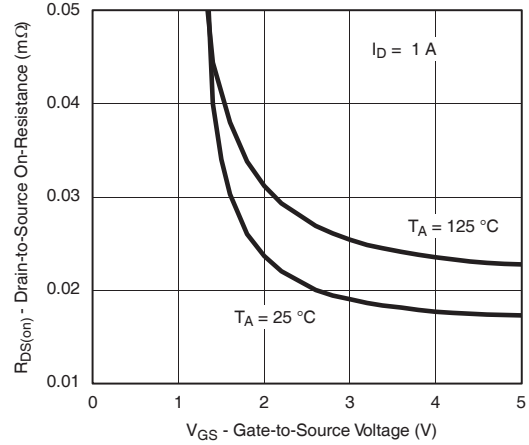


**On-Resistance vs. Junction Temperature**

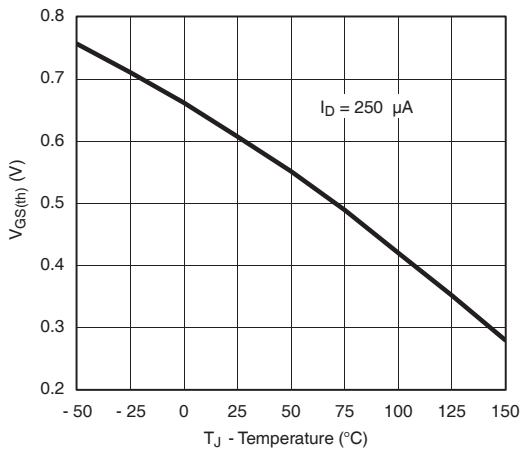
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



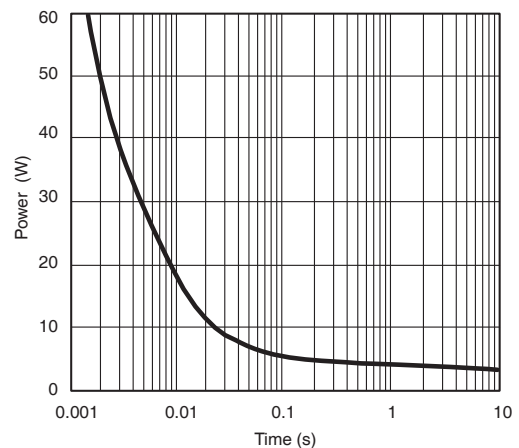
**Source-Drain Diode Forward Voltage**



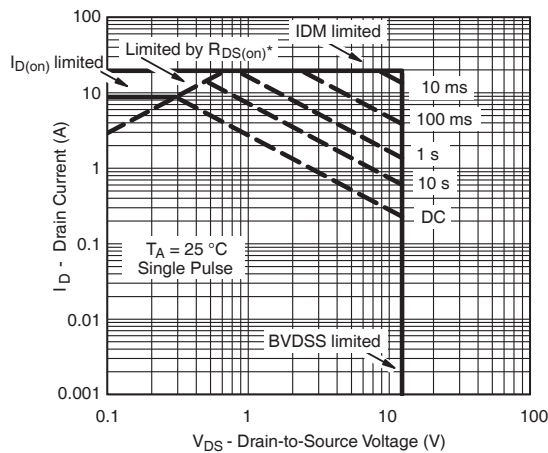
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



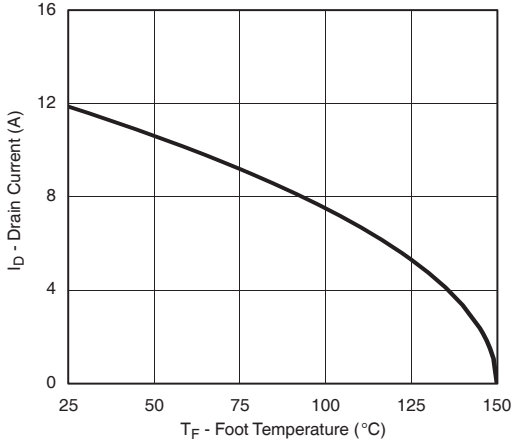
**Single Pulse Power, Junction-to-Ambient**



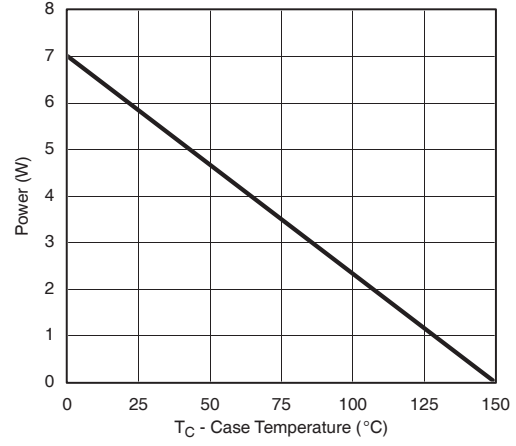
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**Safe Operating Area, Junction-to-Ambient**

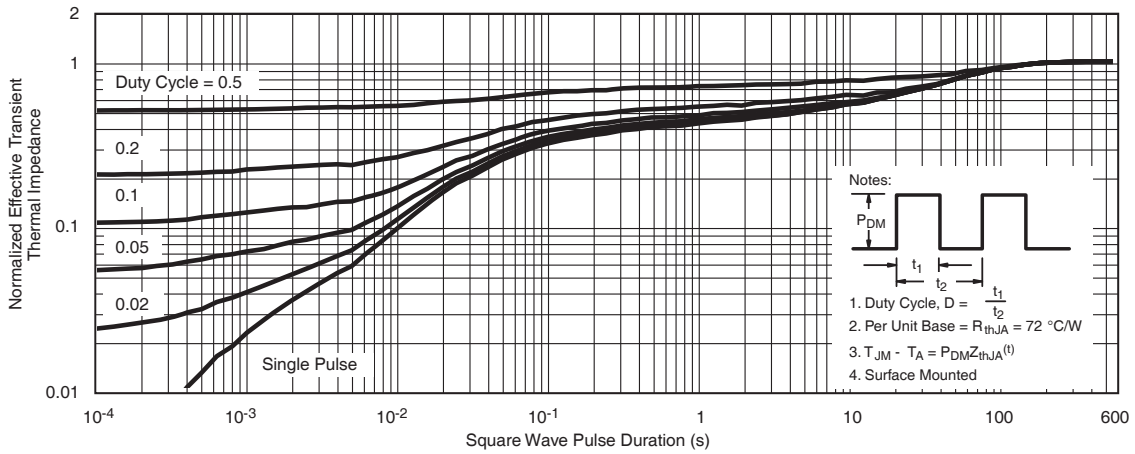
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



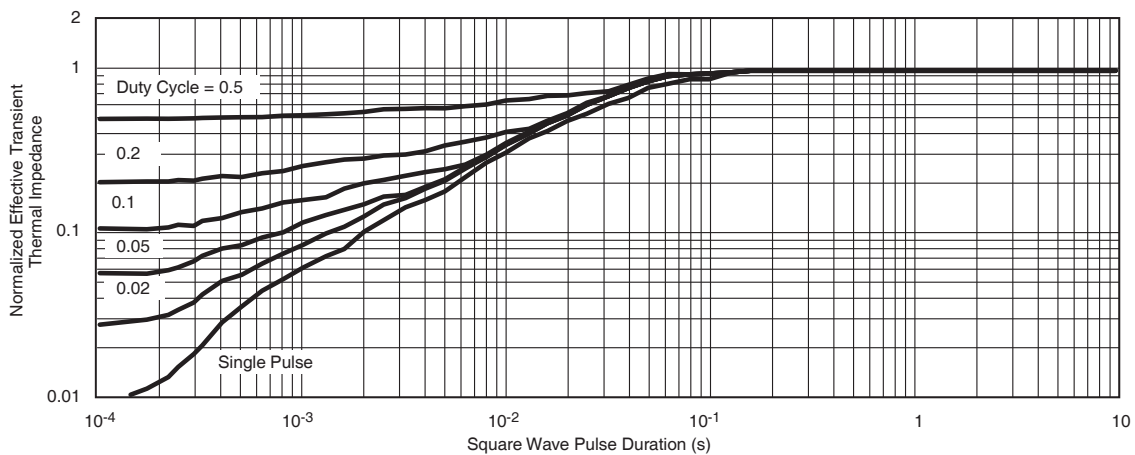
**Current Derating\***



**Power Derating**

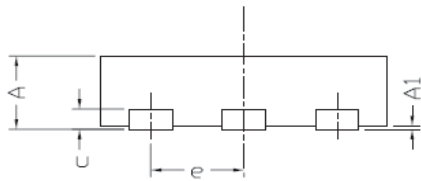
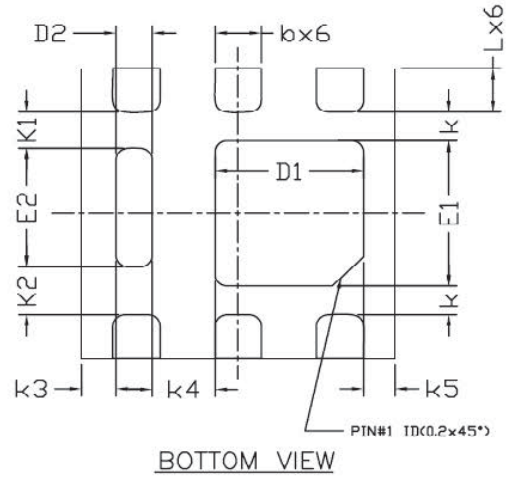
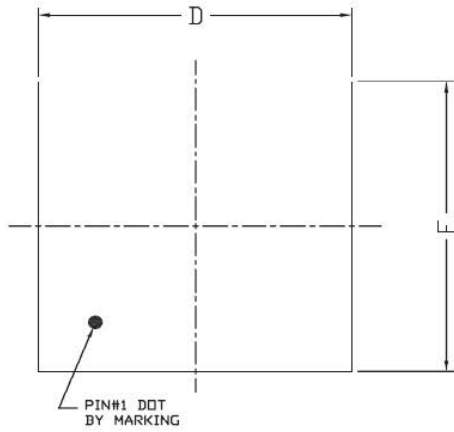


**Normalized Thermal Transient Impedance, Junction-to-Ambient**

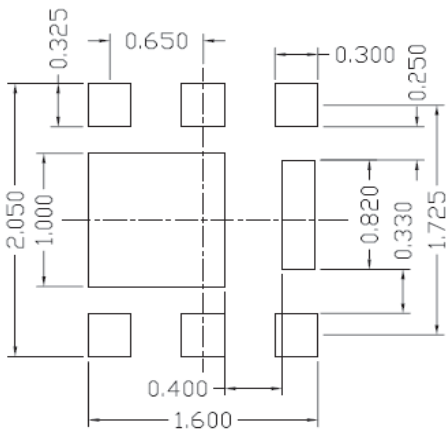


**Normalized Thermal Transient Impedance, Junction-to-Foot**

DFN2x2 \_6L\_EP1\_S PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



UNIT: mm

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.022	0.024
A1	0.00	—	0.05	0.000	—	0.002
b	0.25	0.30	0.35	0.010	0.012	0.014
c	0.152 REF			0.006 REF		
D	1.90	2.00	2.10	0.075	0.079	0.083
D1	0.85	0.95	1.05	0.033	0.037	0.041
D2	0.13	0.23	0.33	0.005	0.009	0.013
E	1.90	2.00	2.10	0.075	0.079	0.083
E1	0.90	1.00	1.10	0.035	0.039	0.043
E2	0.72	0.82	0.92	0.028	0.032	0.036
e	0.65 BSC			0.026 BSC		
K	0.20 BSC			0.008 BSC		
K1	0.25 BSC			0.010 BSC		
K2	0.33 BSC			0.013 BSC		
K3	0.22 BSC			0.009 BSC		
K4	0.40 BSC			0.016 BSC		
K5	0.20 BSC			0.008 BSC		
L	0.25	0.30	0.35	0.010	0.012	0.014

NOTE

1. CONTROLLING DIMENSION IS MILLIMETER.  
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

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